



09/662,682

PATENT APPLICATION

#6/A
7/1/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Li et al.

Serial No.: 09/662,682

Filed: September 15, 2000

For: METAL-ASSISTED CHEMICAL
ETCH POROUS SILICON
FORMATION METHOD

Art Unit: 1765

Examiner: Vinh, Lan

)
) I hereby certify that this paper is being deposited with
) the United States Postal Service as FIRST-CLASS mail
) in an envelope addressed to: Assistant Commissioner
) for Patents, Washington, D.C. 20231, on this date.

) 6/13/02
) Date
) F-CLASS.WCM
) Appr. February 20, 1998

Registration No. 35132
Attorney for Applicant

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AMENDMENT A

Assistant Commissioner for Patents
Washington, D.C. 20231

RECEIVED
JUN 25 2002
TC 1700

Dear Sir:

In response to the office action mailed March 13, 2002, please amend the
application as follows:

In the Specification:

Please replace the paragraph beginning on page 1, line 3 with the following
re-written paragraph:

--STATEMENT OF GOVERNMENT INTEREST

A1